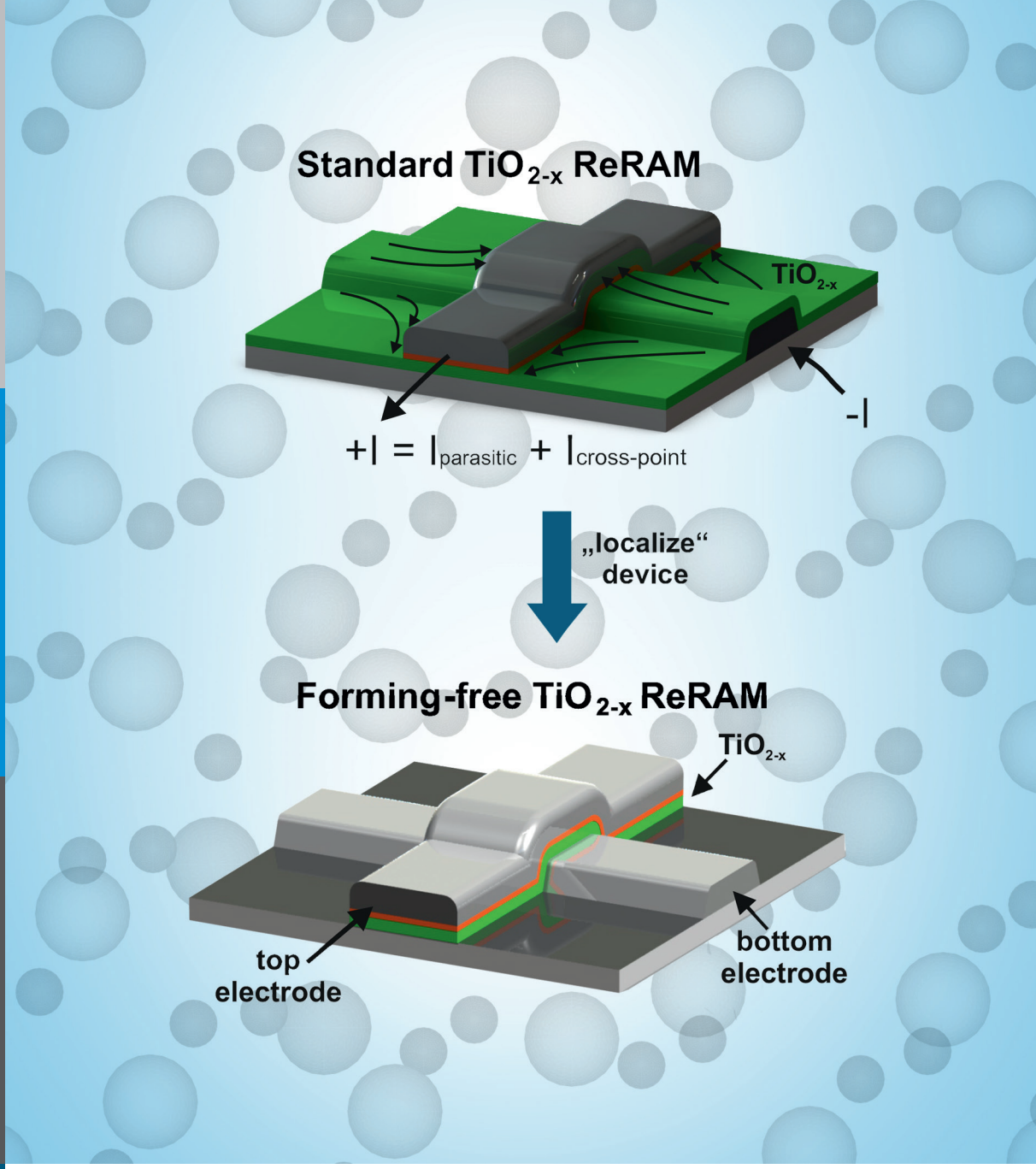

Integration and Characterization of Atomic Layer Deposited TiO_2 Thin Films for Resistive Switching Applications

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Schriften des Forschungszentrums Jülich
Reihe Information / Information Band / Volume 36

ISSN 1866-1777 ISBN 978-3-89336-970-6

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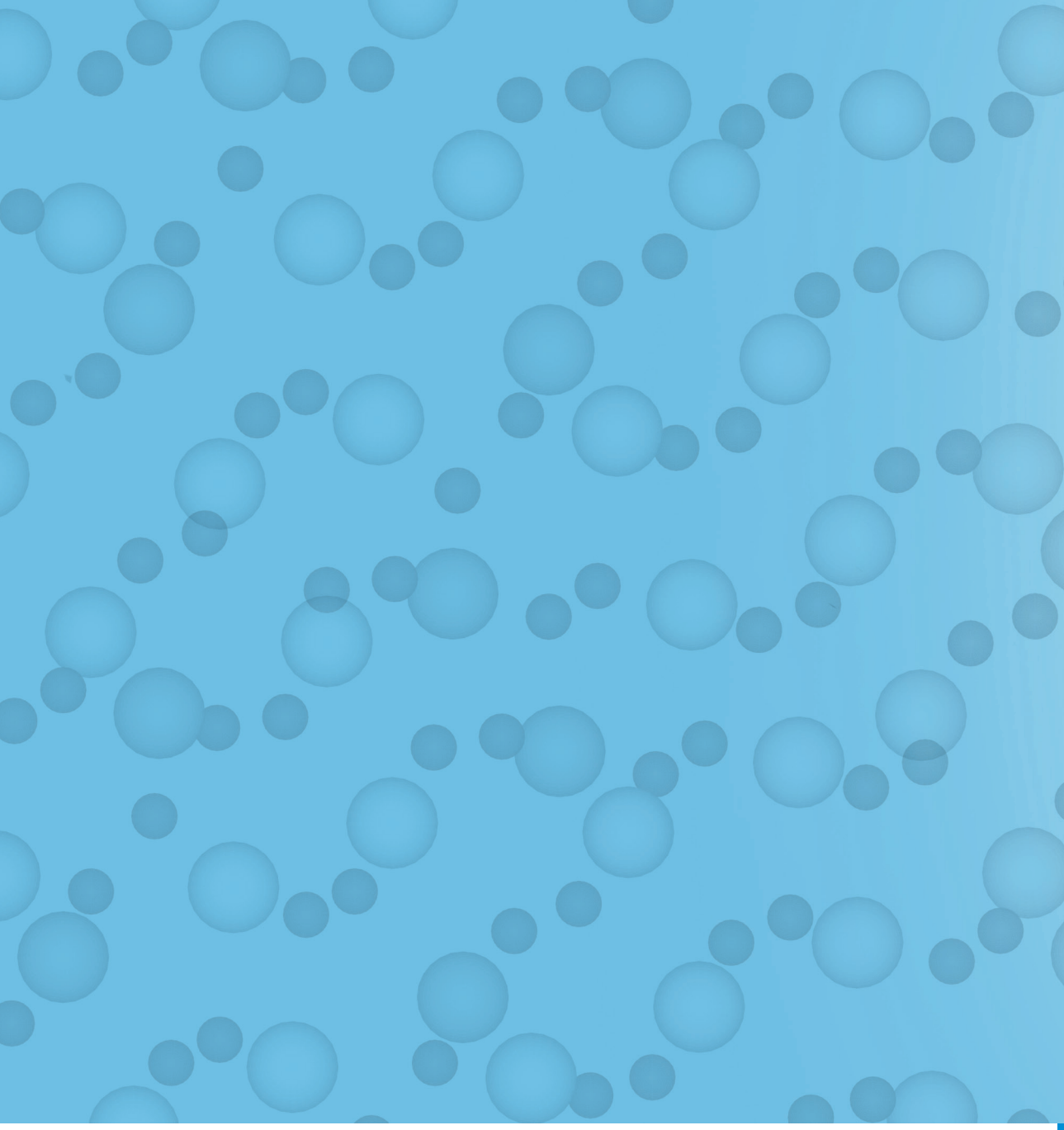

Information / Information
Band / Volume 36
ISBN 978-3-89336-970-6

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